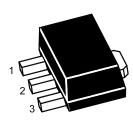
PNP Epitaxial Planar Transistor

High Current Application

The transistor is subdivided into two groups, O and Y, according to its DC current gain.



1.Base 2.Collector 3.Emitter

Absolute Maximum Ratings (T _a = 25 °C)		SOT-89 Plastic Package				
Parameter	Symbol	Value	Unit			
Collector Base Voltage	-V _{CBO}	35	V			
Collector Emitter Voltage	-V _{CEO}	-V _{CEO} 30				
Emitter Base Voltage	-V _{EBO}	-V _{EBO} 5				
Collector Current	-I _C	800	mA			
Base Current	-I _B	160	mA			
Collector Power Dissipation	P _{tot}	500	mW			
Junction Temperature	Tj	150	°C			
Storage Temperature Range	Ts	-55 to +150	°C			

Characteristics at T_{amb} = 25 °C

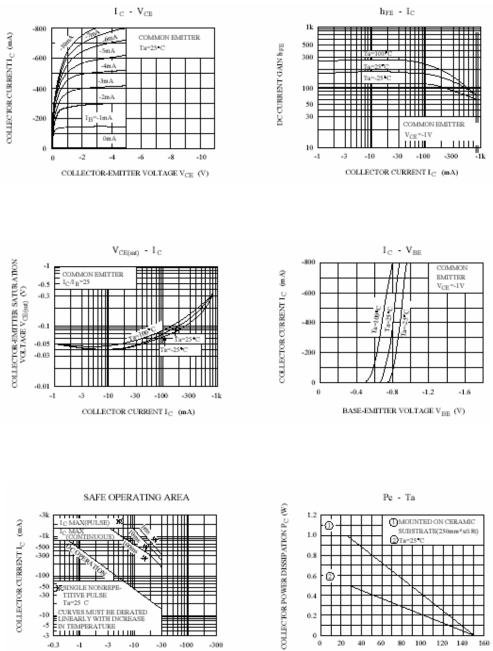
Parameter		Symbol	Min.	Тур.	Max.	Unit
DC Current Gain						
at $-V_{CE} = 1 \text{ V}, -I_{C} = 100 \text{ mA}$	0	h _{FE}	100	-	200	-
	Y	h _{FE}	160	-	320	-
at -V _{CE} = 1 V, -I _C = 700 mA		h _{FE}	35	-	-	-
Collector Cutoff Current at $-V_{CB} = 35 V$		-I _{CBO}	-	-	100	nA
Emitter Cutoff Current at -V _{EB} = 5 V		-I _{EBO}	-	-	100	nA
Collector Emitter Breakdown Voltage at $-I_c = 10 \text{ mA}$		-V _{(BR)CEO}	30	-	-	V
Base Emitter Voltage at -V _{CE} = 1 V, -I _C = 10 mA		-V _{BE}	0.5	-	0.8	V
Collector Output Capacitance at $-V_{CB} = 10 \text{ V}, \text{ f} = 1 \text{ MHz}$		C _{ob}	-	19	-	pF
Collector Emitter Saturation Voltage at $-I_{C} = 500 \text{ mA}$, $-I_{B} = 20 \text{ mA}$		-V _{CE(sat)}	-	-	0.7	V
Transition Frequency at $-V_{CE} = 5 \text{ V}, -I_{C} = 10 \text{ mA}$		f⊤	-	120	-	MHz







Dated : 22/03/2006



AMBIENT TEMPERATURE Ta (*C)



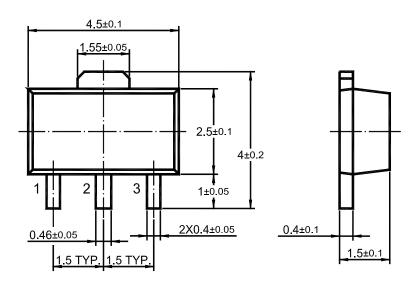
SEMTECH ELECTRONICS LTD. (Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)

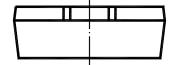
COLLECTOR-EMITTER VOLTAGE VCE (V)



Dated : 22/03/2006

SOT-89 PACKAGE OUTLINE





Dimensions in mm



